

HV255

PRELIMINARY

May 1991

Half Bridge Complementary MOSFET Driver

Features

•	Bipolar	or	Unipolar	Supply	Operation
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- Wide Supply Range ±40V to ±225V
- Complete MOSFET Protection
- High Output to Logic Supply Isolation
- High Peak Output Current2A
- Frequency Range10kHz to 100kHz

Applications

- High Switchmode Power Supplies
- PWM Servo Drives
- Stepper Motor Drives
- DC-DC Converters
- Uninterruptible Power Supplies

Ordering Information

PART NUMBER	TEMPERATURE RANGE	DESCRIPTION	
HV255CP	0°C ≤T _A ≤ +75°C	16 Pin Plastic DIP	
HV255IP	-40°C ≤ T _A ≤ +85°C	16 Pin Plastic DIP	
HV255MJ*	-55°C ≤ T _A ≤+125°C	16 Pin Ceramic DIP	

Description

The HV255 is a monolithic dielectrically isolated high voltage integrated circuit. The circuit provides an interface from digital signals to the gates of complementary power MOSFETs or IGBTs. The circuit has wide supply voltage range, from 80VDC to 450VDC in unipolar connection or +40VDC to +225VDC. In addition the logic supply can float within the high voltage rails.

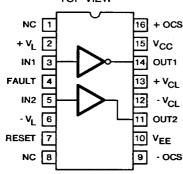
The inputs are TTL compatible when the logic supply is 5V, but will operate up to 15V logic supply.

The outputs provide up to 2A current spikes to drive the gates of power MOSFETs or IGBTs. The actual voltage that the gates are driven to is set by the user, up to 20V for VGS.

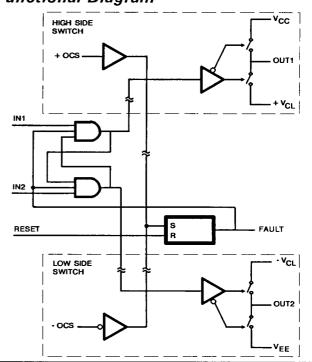
Also on board the chip is an overcurrent sense circuit, which independently sense overcurrent on the high side and the low side. An overcurrent condition sets a latch that disables both outputs. In order to enable the output the reset input must be toggled.

Pinout

HV255CP (16 PIN PLASTIC DIP) TOP VIEW



Functional Diagram



CAUTION: These devices are sensitive to electrostatic discharge. Proper I.C. handling procedures should be followed. Copyright © Harris Corporation 1991 * Offered at a later date.

File Number

2847

Specifications HV255

Absolute Maximum Ratings	Operating Temperature Range
Voltage Between +VS and -VS500V	HV255CP 0°C < T _A < +75°C
Voltage Between +V ₁ and -V ₁	HV255IP40°C < TA < +85°C
Voltage Between -VS and -VI	HV255MJ*55°C < T _A < +125°C
Peak Output Current 2A	Storage Temperature Range65°C < T _A < +150°C
Logic Input Voltage+Vi	Maximum Junction Temperature+175°C
Over Current Sense to VS	,
Fault Output Current 1mA	* Offered at a Later Date

Electrical Specifications $V_{CC} = +40V$, $V_{EE} = -40V$, $C_L = 10$ nF, $V_L = 5V$ Unless Otherwise Specified

		HV2	HV255CP, HV255IP		
PARAMETER	ТЕМР	MIN	TYP	MAX	UNITS
INPUT CHARACTERISTICS		<u> </u>			•
Input Voltage, High (VIH)	Full	2.4	_	T -	l v
Input Voltage, Low (VIL)	Full	_	_	0.8	v
Input Current (I _{IH})	+25°C	-	_	300	μΑ
	Full	_	_	300	μА
Input Current, Low (I _{IL})	+25°C	150	_	_	μА
	Full	150	-	_	ДA
Overcurrent Input Threshold	+25°C	80	100	120	mV
	Fuli	75	100	125	mV
TRANSFER CHARACTERISTICS				•	*
Turn-On Delay (T _{D1} , T _{D3})	+25°C	-	-	1	μѕ
	Full	-	-	1	μs
Turn-On Delay Skew (T _{D1} , T _{D3})	+25°C	-	±300	_	ns
	Full	_	±300	-	ns
Turn-Off Delay (T _{D2} , T _{D4})	+25°C	_	-	1	μs
	Full	_	-	1	μs
Turn-Off Delay Skew (T _{D2} , T _{D4})	+25°C	_	±100	-	ns
	Full	_	±100	-	ns
Current Limit Sense to Output Turn-Off Delay	+25°C	-	500	-	ns
	Full	_	500	_	ns
Current Limit Sense to Fault Output Turn-Off Delay	+25°C	50	-	150	ns
	Full	50	-	150	ns
Reset Delay (T _{D6})	+25°C	-	500	_	ns
	Full	_	500	-	ns
OUTPUT CHARACTERISTICS					
Output Rise Time	Full	-	100	150	ns
Output Fall Time	Full	-	100	150	ns
OUT1 Voltage (High)	Full	+V _S -0.2	-	-	V
OUT1 Voltage (Low)	Full	-	-	+V _S -19	V
OUT2 Voltage (High)	Full	-V _S +19	-		V
OUT2 Voltage (Low)	Full	-	-	-V _S +0.2	V
Fault Output (VOH)	Full	4.5	-	-	V
Fault Output (V _{OL})	Full		_	0.8	V
POWER SUPPLY	··· 				
lcc	Full	-	-	200	μА
¹ EE	Full	-	-	200	μΑ
IL.	Full	-	-	4	mA

Parameter Definitions (Refer to Switching Waveforms)

SYMBOL	DEFINITIONS
T _{D2}	Delay time as measured from the logic input high to low transition (1 to 0) at the 10% point, to the 10% point of the output transition for the high side switch.
T _{D1}	Delay time as measured from the logic input low to high transition (0 to 1) at the 10% point, to the 10% point of the output transition for the high side switch.
T _{D4}	Same as T _{DO-1} for the ow side switch.
трз	Same as T _{D1-1} for the ow side switch.
T _{R1}	Output rise time from the 10% – 90% points for the high side switch.
T _{R2}	Output rise time from the 10% - 90% points for the low side switch.
T _{F1}	Output fall time from the 10% - 90% points for the high side switch.
T _{F2}	Output fall time from the 10% - 90% points for the low side switch.
T _{D5}	Delay time as measured from the overcurrent input 10% point to the fault output high to low transition at the 10% point.
T _{D6}	Delay time as measured from the reset input 10% point to the fault output low to high transition at the 90% point.
T _{D7}	Delay time as measured from the overcurrent 1 input 10% point to output 1 low to high transition at the 90% point.
T _{D8}	Delay time as measured from the overcurrent 2 input 10% point to output 2 high to low transition at the 10% point.

Switching Time Test Circuits

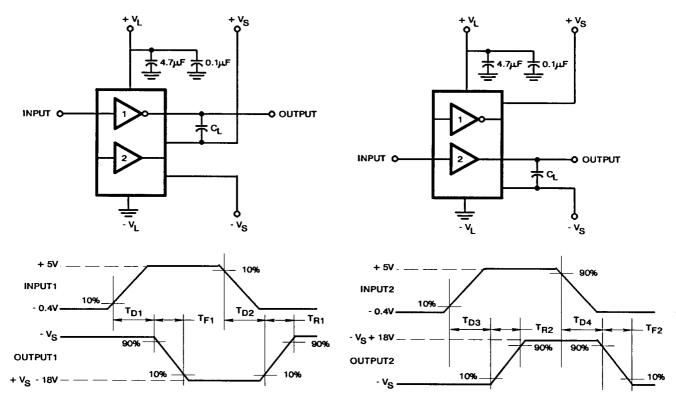
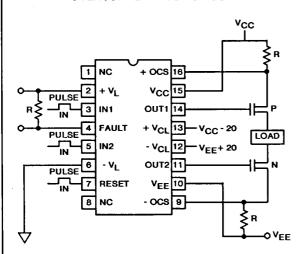


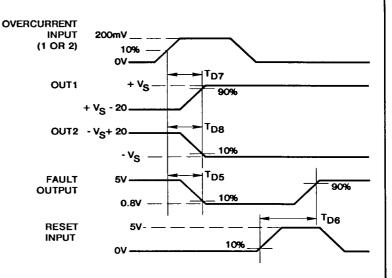
FIGURE 1. INVERTING DRIVE SWITCHING TIME (HIGH SIDE)

FIGURE 2. NON-INVERTING DRIVER SWITCHING TIME (LOW SIDE)

Overcurrent Test Waveforms

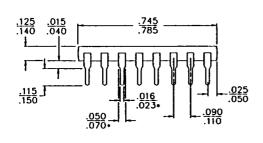
OVERCURRENT TEST CIRCUIT

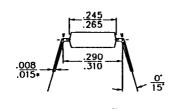




Packaging

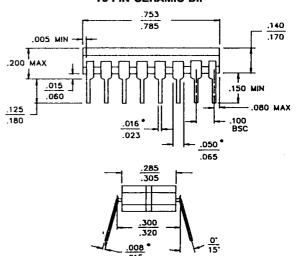
16 PIN PLASTIC DIP





ADD .003 INCHES TO DIM FOR SOLDER DIPPED LEADS.

16 PIN CERAMIC DIP



• INCREASE MAX LIMIT BY .003 INCHES MEASURED AT CENTER OF FLAT FOR

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Sales Office Headquarters

UNITED STATES

Harris Semiconductor 1301 Woody Burke Road Melbourne, Florida 32902 TEL: (407) 724-3739

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Harris Semiconductor Mercure Centre Rue de la Fusee 100 1130 Brussels, Belgium TEL: (32) 2-246-21.11

SOUTH ASIA

Harris Semiconductor H.K. Ltd 13/F Fourseas Building 208-212 Nathan Road Tsimshatsui, Kowloon Hong Kong TEL: (852) 3-723-6339

NORTH ASIA Harris K.K. Shinjuku NS Bldg. Box 6153 2-4-1 Nishi-Shinjuku Shinjuku-Ku, Tokyo 163 Japan TEL: (81) 03-3345-8911



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